

SiHD9N60E-VB Datasheet

N-Channel 600V (D-S) Super Junction Power MOSFET

PRODUCT SUMMARY

V_{DS} (V) at T_J max.	600	
$R_{DS(on)}$ typ. (Ω) at 25 °C	$V_{GS} = 10$ V	0.340

FEATURES

- Low figure-of-merit (FOM) $R_{on} \times Q_g$
- Low input capacitance (C_{iss})
- Reduced switching and conduction losses
- Ultra low gate charge (Q_g)
- Avalanche energy rated (UIS)

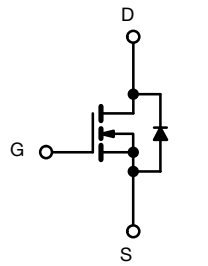


RoHS
COMPLIANT
HALOGEN
FREE

TO-252



Top View



N-Channel MOSFET

APPLICATIONS

- Server and telecom power supplies
- Switch mode power supplies (SMPS)
- Power factor correction power supplies (PFC)
- Lighting
 - High-intensity discharge (HID)
 - Fluorescent ballast lighting
- Industrial
 - Welding
 - Induction heating
 - Motor drives
 - Battery chargers
 - Renewable energy
 - Solar (PV inverters)

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

PARAMETER			SYMBOL	LIMIT	UNIT
Drain-source voltage			V_{DS}	600	V
Gate-source voltage			V_{GS}	± 30	
Continuous drain current ($T_J = 150\text{ }^{\circ}\text{C}$)	V_{GS} at 10 V	$T_C = 25\text{ }^{\circ}\text{C}$	I_D	12	A
		$T_C = 100\text{ }^{\circ}\text{C}$		7	
Pulsed drain current ^a			I_{DM}	36	
Linear derating factor				1.7	W/ $^{\circ}\text{C}$
Single pulse avalanche energy ^b			E_{AS}	310	mJ
Maximum power dissipation			P_D	180	W
Operating junction and storage temperature range			T_J, T_{stg}	-55 to +150	$^{\circ}\text{C}$
Drain-source voltage slope	$T_J = 125\text{ }^{\circ}\text{C}$		dV/dt	50	V/ns
Reverse diode dV/dt ^d				5.1	
Soldering recommendations (peak temperature) ^c	For 10 s			260	$^{\circ}\text{C}$

Notes

- Repetitive rating; pulse width limited by maximum junction temperature
- $V_{DD} = 100$ V, starting $T_J = 25$ °C, $L = 30$ mH, $R_g = 25$ Ω , $I_{AS} = 6$ A
- 1.6 mm from case
- $I_{SD} \leq I_D$, $dI/dt = 100$ A/ μ s, starting $T_J = 25$ °C

THERMAL RESISTANCE RATINGS

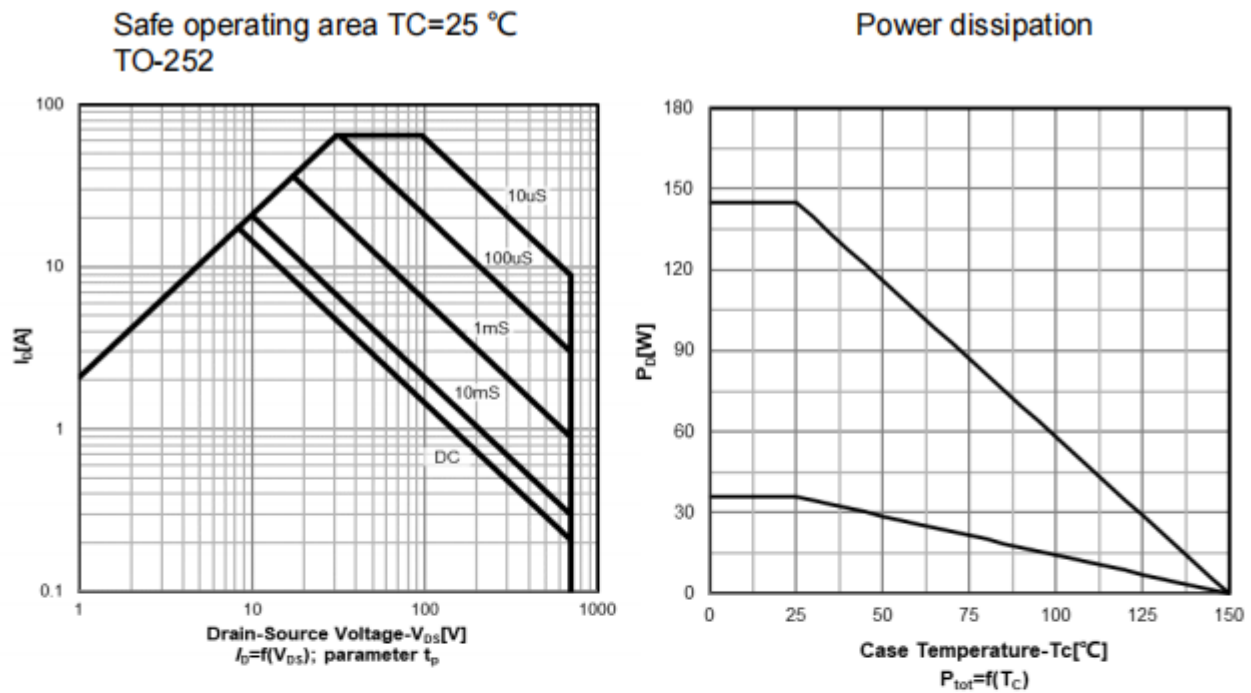
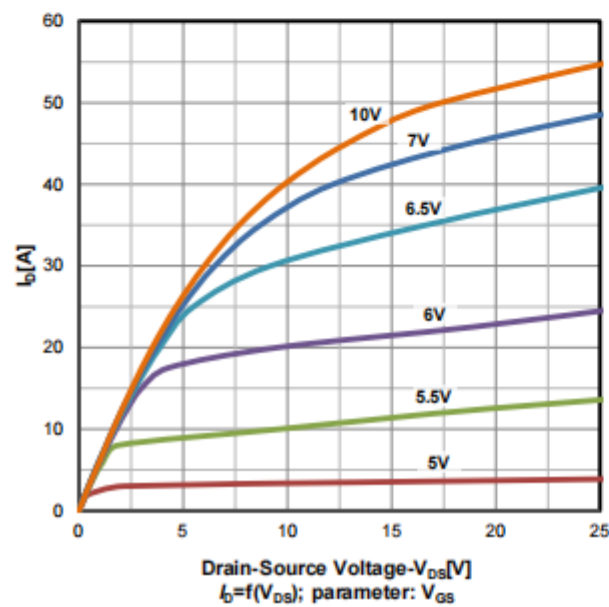
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum junction-to-ambient	R_{thJA}	-	62	°C/W
Maximum junction-to-case (drain)	R_{thJC}	-	0.85	

SPECIFICATIONS ($T_J = 25\text{ °C}$, unless otherwise noted)

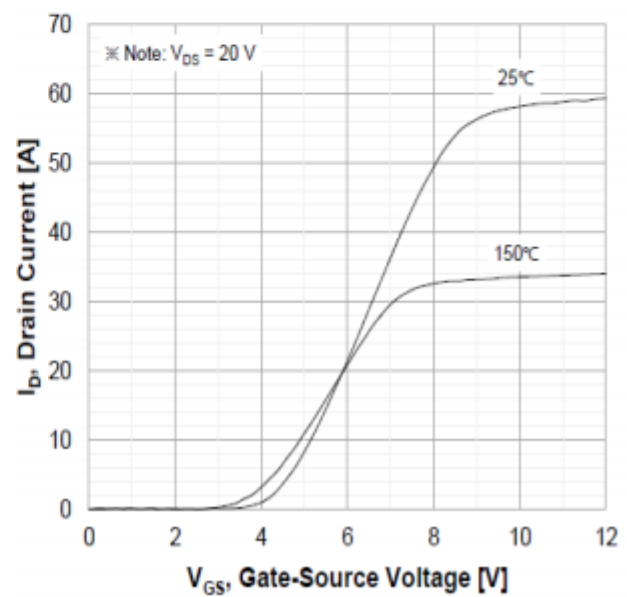
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0\text{ V}$, $I_D = 250\text{ }\mu\text{A}$		600	-	-	V
V_{DS} temperature coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^{\circ}\text{C}$, $I_D = 1\text{ mA}$		-	1.08	-	V/ $^{\circ}\text{C}$
Gate-source threshold Voltage (N)	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$		2.0	-	4.0	V
Gate-source leakage	I_{GSS}	$V_{GS} = \pm 20\text{ V}$		-	-	± 100	nA
		$V_{GS} = \pm 30\text{ V}$		-	-	± 1	μA
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 600\text{ V}$, $V_{GS} = 0\text{ V}$		-	-	1	μA
		$V_{DS} = 480\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 125\text{ }^{\circ}\text{C}$		-	-	10	
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 4\text{ A}$	-	0.340	-	Ω
Forward transconductance	g_{fs}	$V_{DS} = 30\text{ V}$, $I_D = 12\text{ A}$		-	8.7	-	S
Dynamic							
Input capacitance	C_{iss}	$V_{GS} = 0\text{ V}$, $V_{DS} = 100\text{ V}$, $f = 1\text{ MHz}$		-	1500	-	pF
Output capacitance	C_{oss}			-	51	-	
Reverse transfer capacitance	C_{rss}			-	12	-	
Effective output capacitance, energy related ^a	$C_{o(er)}$	$V_{DS} = 0\text{ V to } 480\text{ V}$, $V_{GS} = 0\text{ V}$		-	50	-	
Effective output capacitance, time related ^b	$C_{o(tr)}$			-	205	-	
Total gate charge	Q_g	$V_{GS} = 10\text{ V}$	$I_D = 12\text{ A}$, $V_{DS} = 480\text{ V}$	-	25	-	nC
Gate-source charge	Q_{gs}			-	8	-	
Gate-drain charge	Q_{gd}			-	10	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 480\text{ V}$, $I_D = 12\text{ A}$, $V_{GS} = 10\text{ V}$, $R_g = 9.1\text{ }\Omega$		-	12	24	ns
Rise time	t_r			-	14	23	
Turn-off delay time	$t_{d(off)}$			-	61	110	
Fall time	t_f			-	16	-	
Gate input resistance	R_g	$f = 1\text{ MHz}$, open drain		0.3	0.7	1.4	Ω
Drain-Source Body Diode Characteristics							
Continuous source-drain diode current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	12	A
Pulsed diode forward current	I_{SM}			-	-	36	
Diode forward voltage	V_{SD}	$T_J = 25\text{ }^{\circ}\text{C}$, $I_S = 12\text{ A}$, $V_{GS} = 0\text{ V}$		-	-	1.2	V
Reverse recovery time	t_{rr}	$T_J = 25\text{ }^{\circ}\text{C}$, $I_F = I_S = 12\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_R = 25\text{ V}$		-	416	832	ns
Reverse recovery charge	Q_{rr}			-	6.4	12.8	μC
Reverse recovery current	I_{RRM}			-	27	-	A

Notes

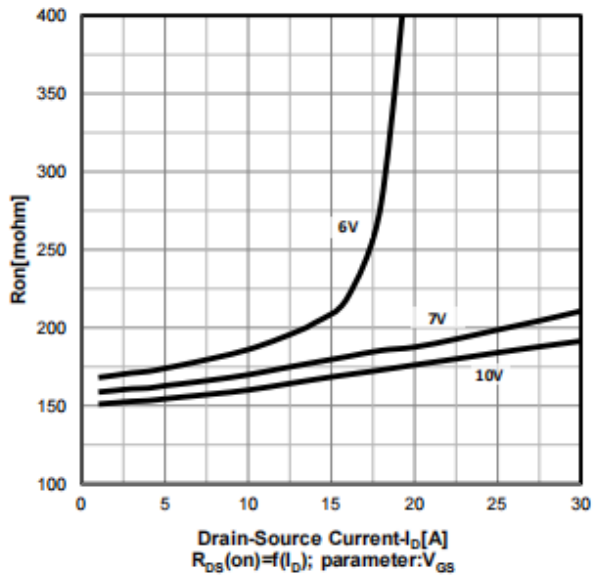
- a. $C_{oss(er)}$ is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS}
 b. $C_{oss(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS}

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

 Typ. output characteristics $T_J = 25\text{ °C}$


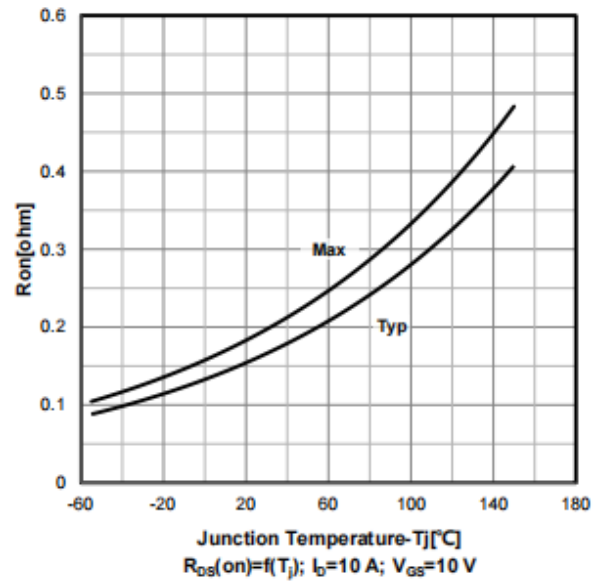
Transfer characteristics



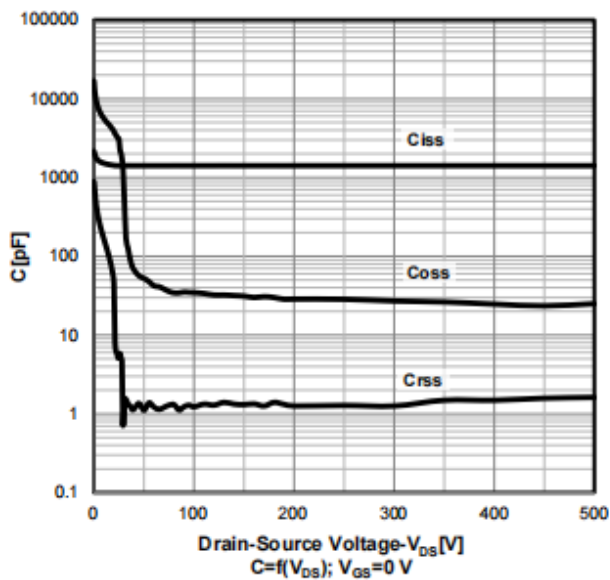
Typ. drain-source on-state resistance



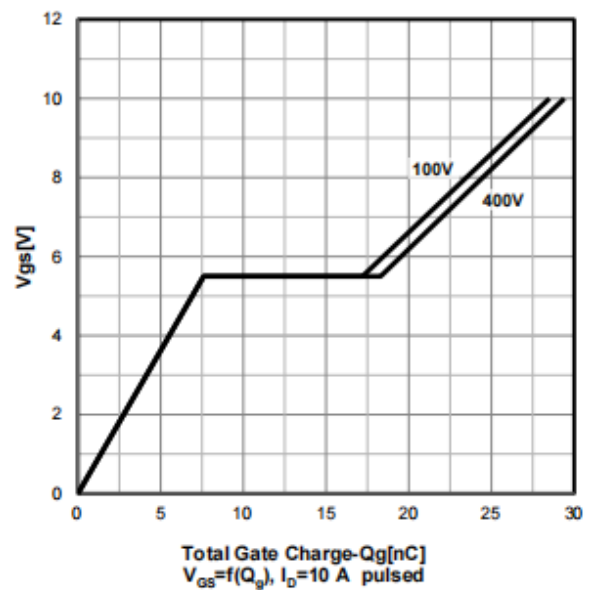
On-resistance vs temperature



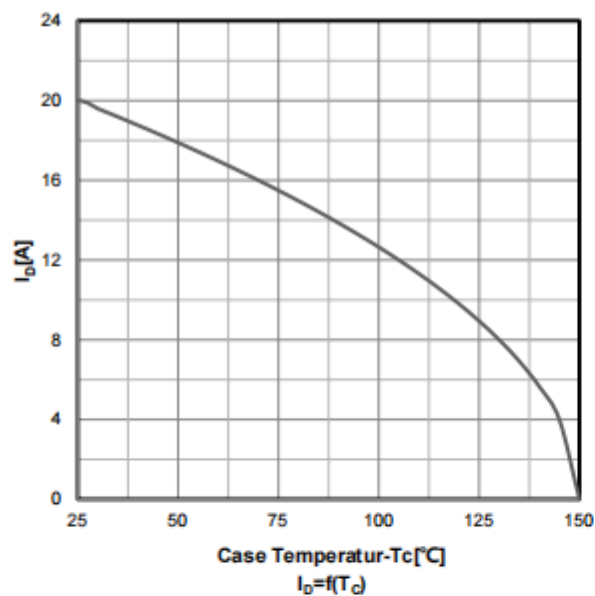
Typ. capacitances



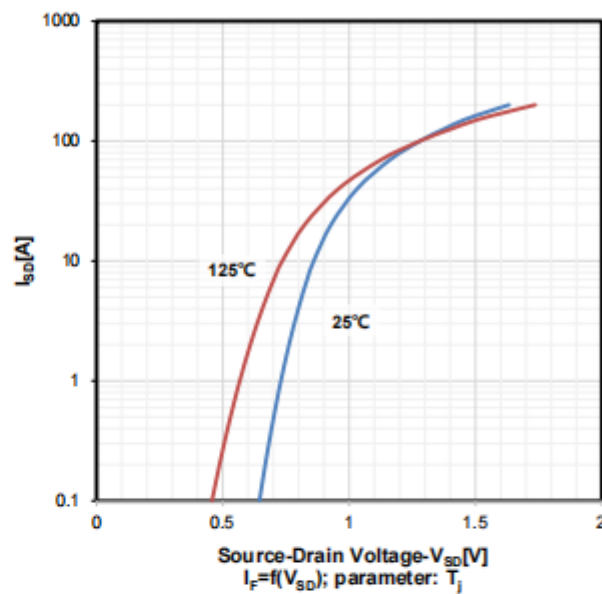
Typ. gate charge characteristics



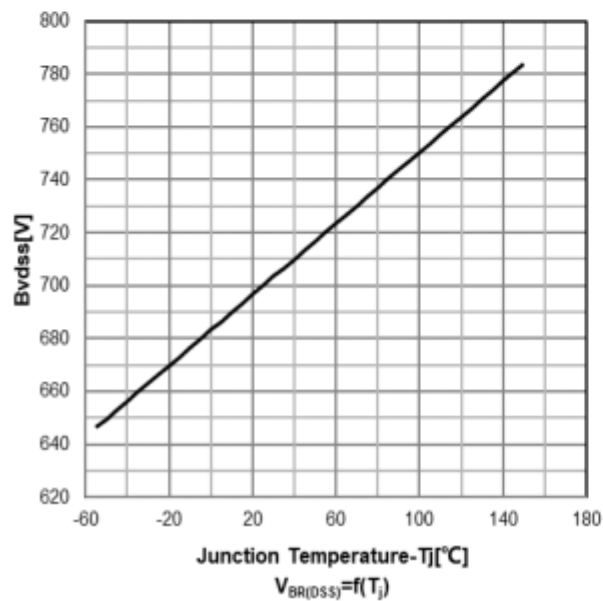
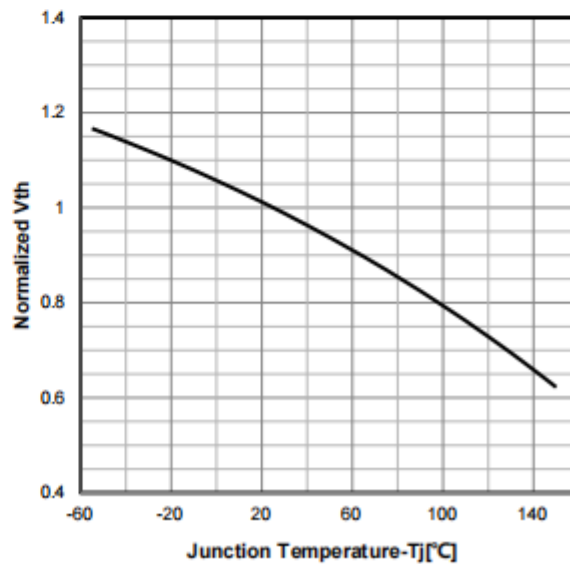
Drain current vs temperature



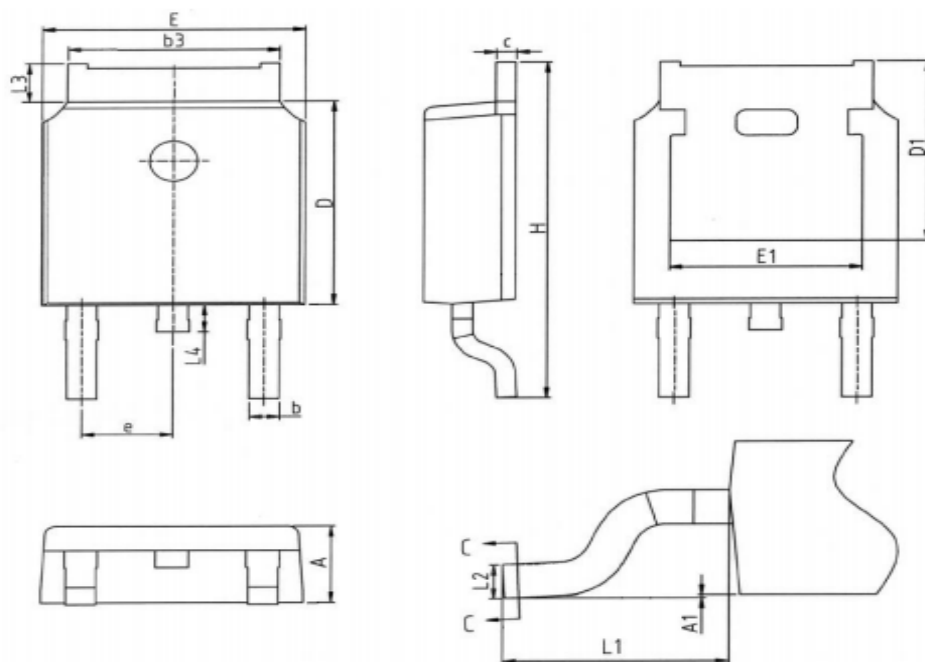
Forward characteristics of reverse diode



Drain-source breakdown voltage

Normalized $V_{GS(th)}$ characteristics

Package Outline : TO 252



COMMON DIMENSIONS

SYMBOL	UNIT(mm)		
	MIN	NOM	MAX
A	2.20	2.30	2.40
A1	0.00	-	0.127
b	0.66	0.78	0.90
b3	5.16	5.31	5.46
c	0.43	0.53	0.63
D	5.98	6.10	6.22
D1	5.30REF		
E	6.40	6.60	6.75
E1	4.63	-	-
e	2.286BSC		
H	9.40	10.10	10.50
L1	2.90REF		
L2	0.51BSC		
L3	0.88	1.08	1.28
L4	0.50	0.80	1.00

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